

BRCS100N06BD

Rev.A May.-2019

描述 / Descriptions

N 沟道 TO-263 塑封封装场效应管。

N-CHANNEL MOSFET in a TO-263 Plastic Package.

特征 / Features

低栅电荷,低反馈电容,开关速度快。

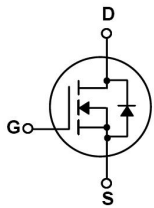
Low gate charge, low crss, fast switching.

用途 / Applications

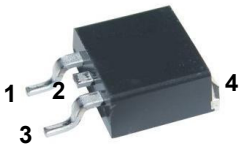
用于高功率 DC/DC 转换和功率开关。

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : G

PIN 2、4 : D

PIN 3 : S

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain Current	$I_D(T_C=25^\circ C)$	100	A
Peak Drain Current	I_{DM}	380	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulsed Avalanche Energy	E_{AS}	602	mJ
Avalanche Current	I_{AS}	38.9	A
Total Power Dissipation	$P_D(T_C=25^\circ C)$	188	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$
Thermal Resistance-Junction to Case	$R_{\theta JC}$	0.8	$^\circ C/W$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	62.5	

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V$ $V_{GS}=0V$			1	μA
		$V_{DS}=60V$ $V_{GS}=0V$ $T_J=125^\circ C$			10	μA
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2	2.6	4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V$ $I_D=50A$		5.9	7	$m\Omega$

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Diode Forward Voltage	V_{SD}	$I_S=1A$ $V_{GS}=0V$		0.6	1.2	V
Input Capacitance	C_{iss}	$V_{GS}=0V$ $V_{DS}=25V,$ $f=1.0MHz$		4920		pF
Output Capacitance	C_{oss}			295		
Reverse Transfer Capacitance	C_{rss}			133		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V,$ $f=1MHz$		1.2		Ω
Total Gate Charge	$Q_g(10V)$	$V_{GS}=10V$ $V_{DS}=30V$ $I_D=50A$		53	75	nC
Total Gate Charge	$Q_g(4.5V)$			22	31	
Gate Source Charge	Q_{gs}			17		
Gate Drain Charge	Q_{gd}			5		
Turn-On DelayTime	$t_{D(on)}$	$V_{DD}=30V$ $I_D=50A$ $V_{GS}=10V$ $R_G=2.5\Omega$		18		ns
Turn-On Rise Time	t_r			20		
Turn-Off DelayTime	$t_{D(off)}$			33		
Turn-Off Fall Time	t_f			4		

A. The value of R_{qJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ C$. The Power dissipation PDSM is based on R_{qJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.

B. The power dissipation PD is based on $T_{J(MAX)}=150^\circ C$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ C$.

D. The R_{qJA} is the sum of the thermal impedance from junction to case R_{qJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300ms pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=150^\circ C$. The SOA curve provides a single pulse rating.

G. The maximum current limited by package.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ C$.

电参数曲线图 / Electrical Characteristic Curve

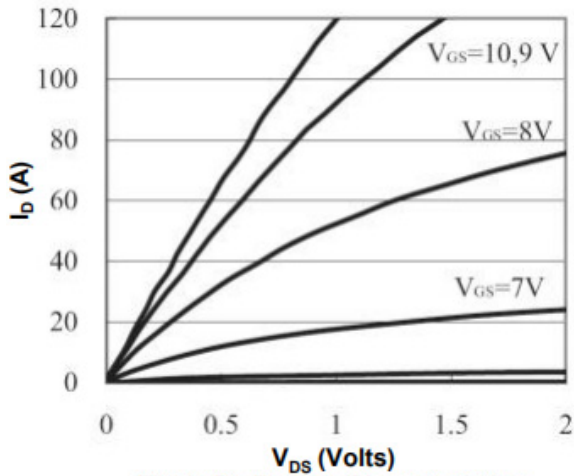


Fig 1: On-Region Characteristics

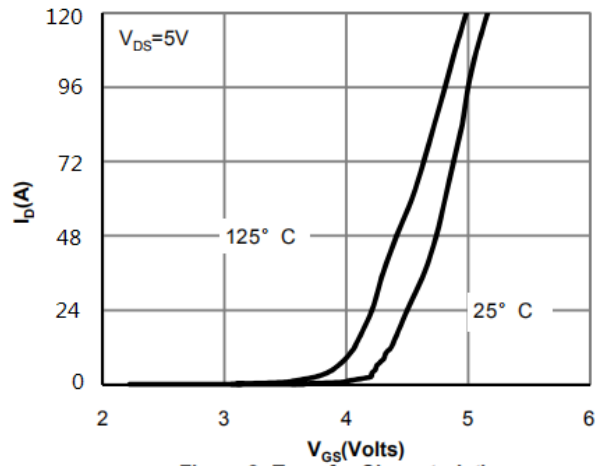


Figure 2: Transfer Characteristics

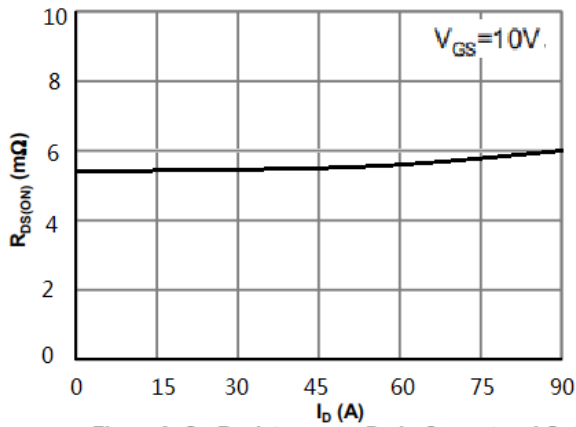


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

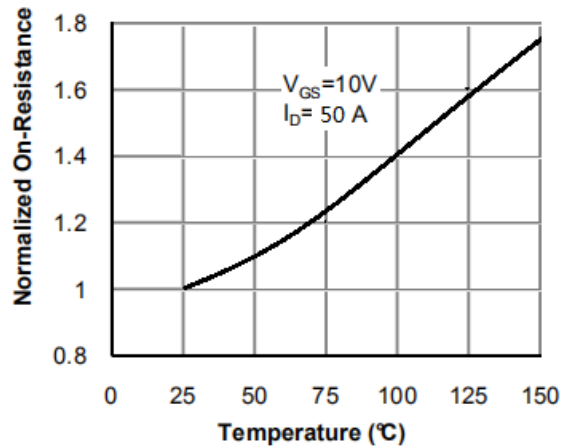


Figure 4: On-Resistance vs. Junction Temperature

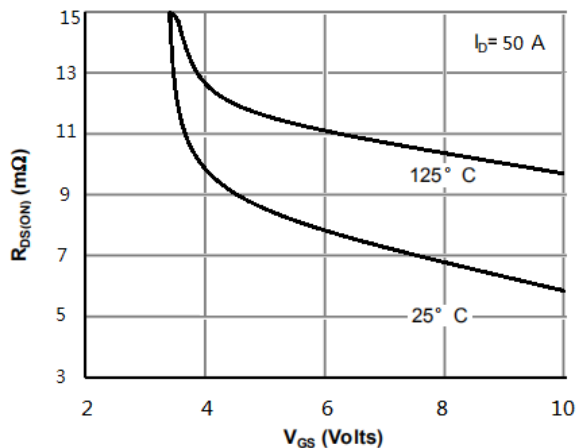


Figure 5: On-Resistance vs. Gate-Source Voltage

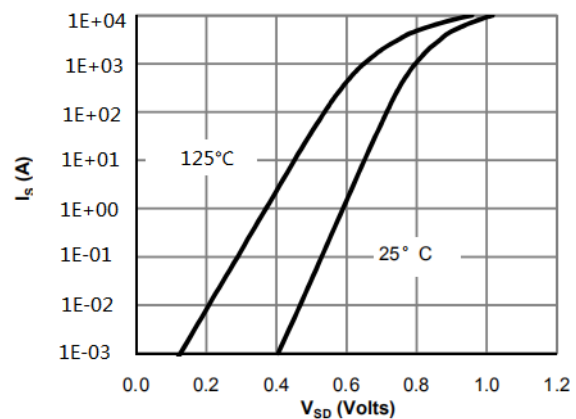


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

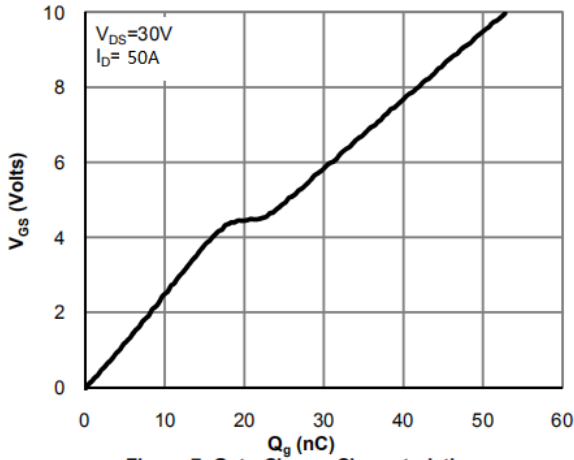


Figure 7: Gate-Charge Characteristics

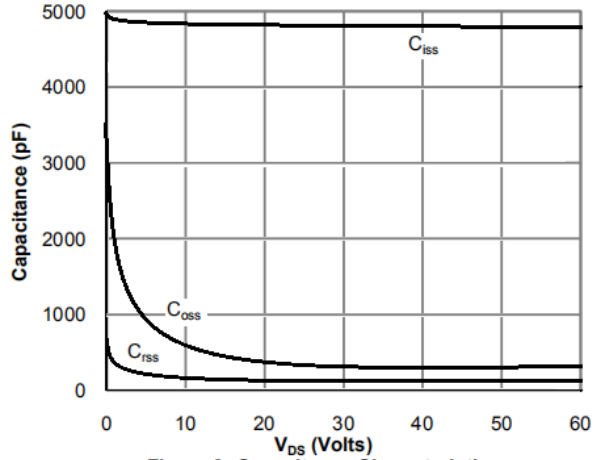


Figure 8: Capacitance Characteristics

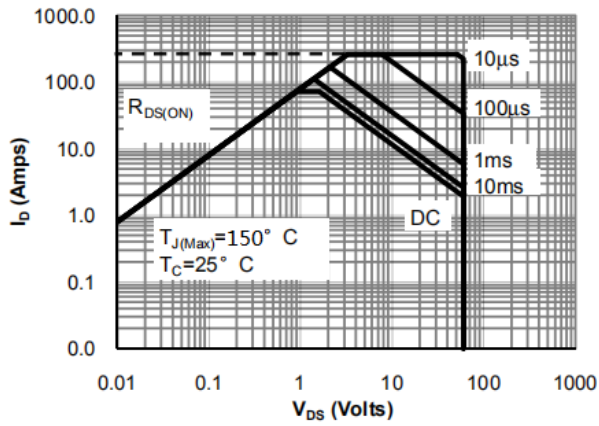


Figure 9: Maximum Forward Biased Safe Operating Area

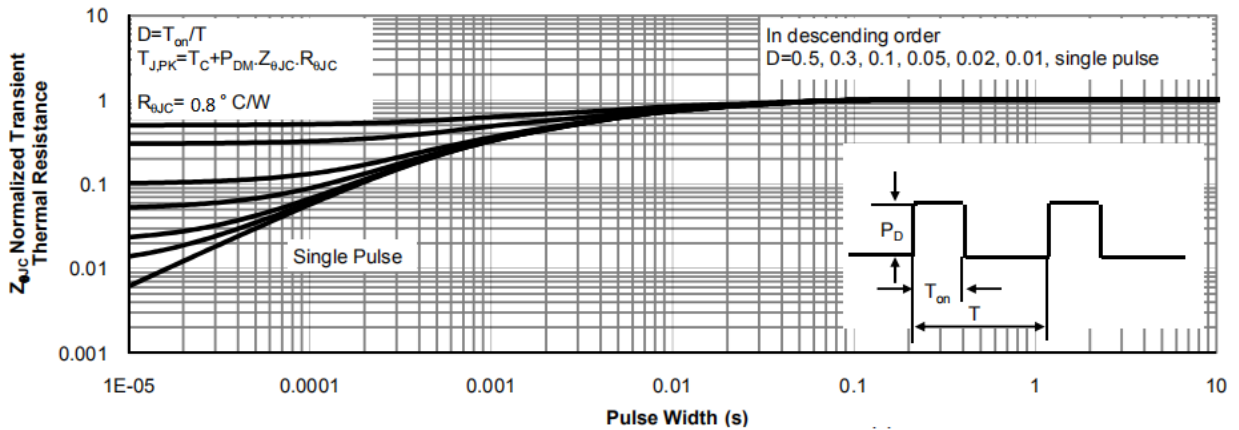
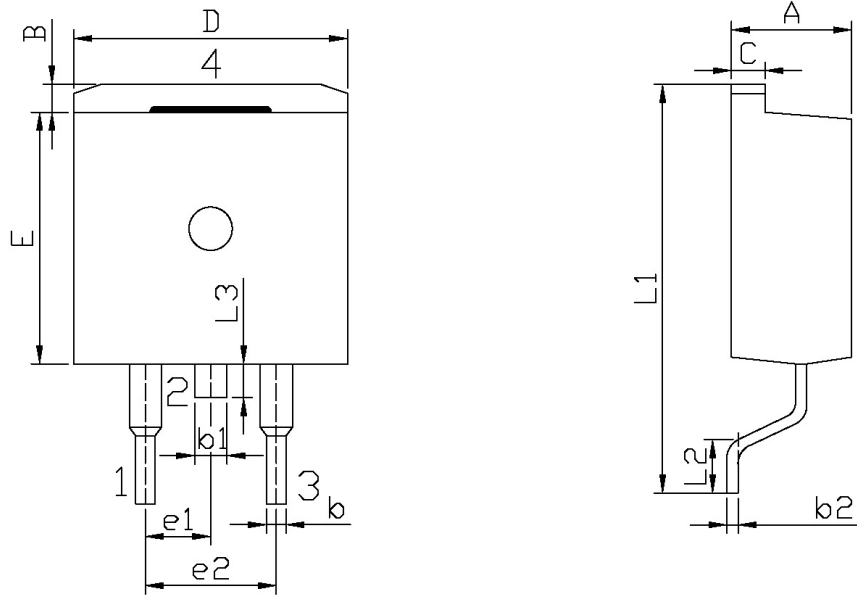


Figure 10 : Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

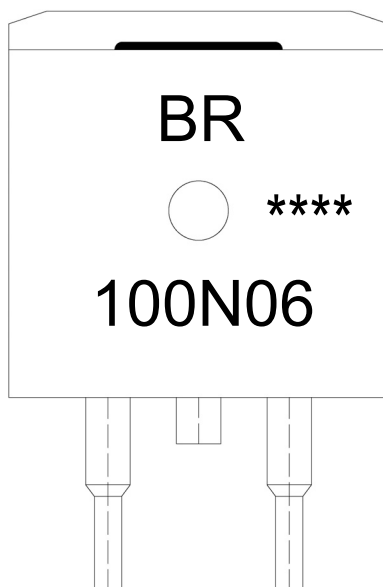


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.34	2.74
b	0.70	0.90	e2	4.88	5.28
b1	1.15	1.35	L1	15.00	16.00
b2	0.40	0.60	L2	2.24	2.84
C	1.20	1.40	L3	1.20	1.60
D	9.80	10.20			

T0-263

印章说明 / Marking Instructions



说明：

BR： 为公司代码

100N06： 为型号代码

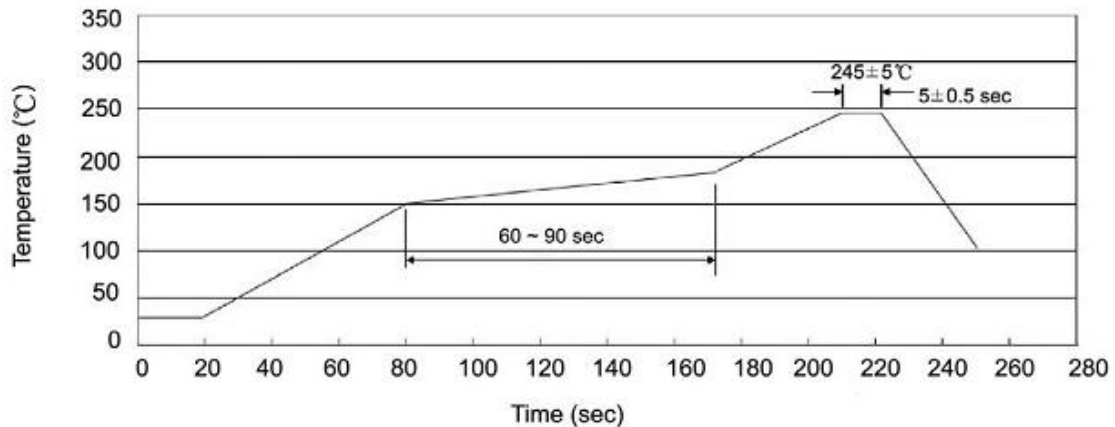
****： 为生产批号代码，随生产批号变化。

Note:

BR: Company Code

100N06: Product Type.

****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-263	800	1	800	5	4,000	13" ×24	360×360×50	385×257×392

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-263	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180

使用说明 / Notices